

(T_j=25 unless otherwise specified)

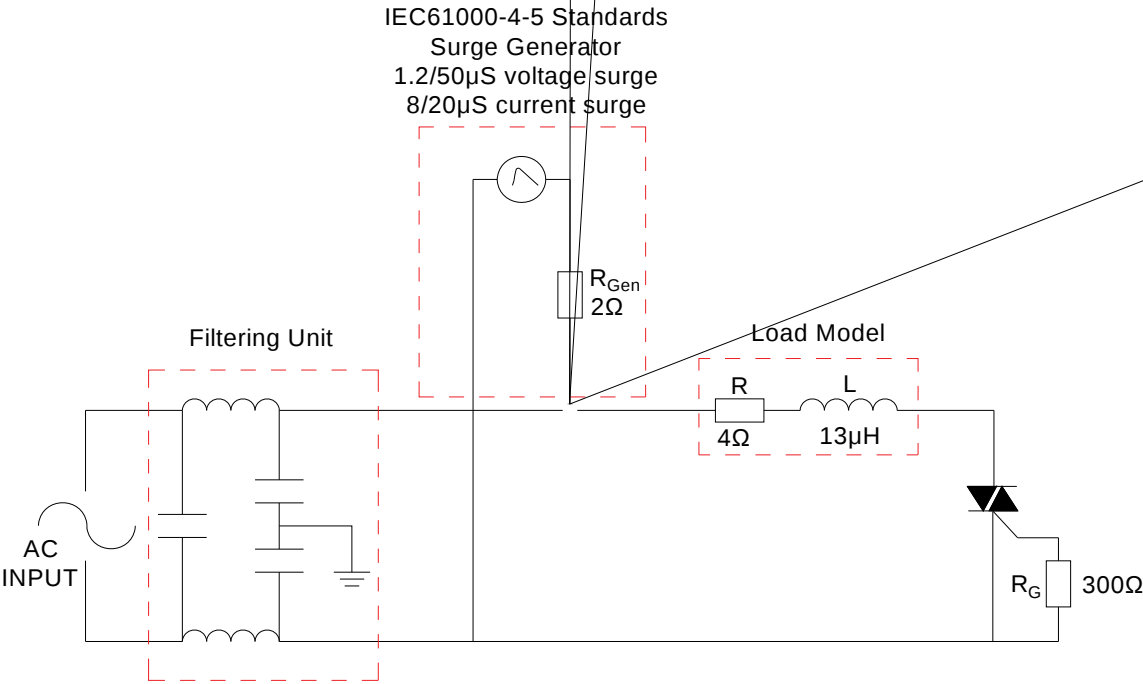
Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	- -	MAX.	25	mA
				70	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3kΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	40	mA
				90	
I _H	I _T =500mA		MAX.	40	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	200	V/μs
(dV/dt) _c	(dI/dt) _c =5A/ms, T _j =110		MIN.	8	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25		TYP.	5	μs
t _{off}				30	

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =15A t _p =380μs	T _j =25	1.6	V
V _{TO}	Threshold voltage	T _j =125	0.8	V
R _D	Dynamic resistance	T _j =125	41	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25	5	μA
I _{RRM}		T _j =125	0.5	mA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	3	/W
R _{th(j-a)}	junction to ambient (AC)	100	/W

J ST 138 H -800 F

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.